

Sonic Fast Recovery Diode

V_{RRM} = 600 V
 I_{FAV} = 2x 30 A
 t_{rr} = 40 ns

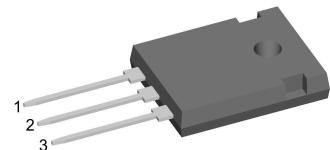
High Performance Fast Recovery Diode

Low Loss and Soft Recovery

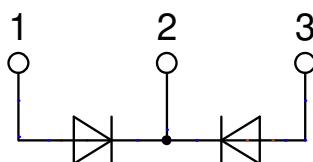
Common Cathode

Part number

DHG60C600HB



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

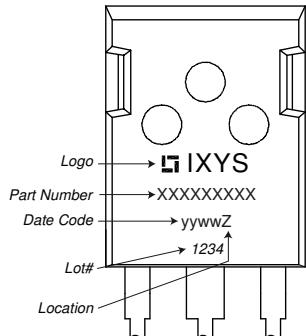
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Fast Diode

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			600	V
I_R	reverse current, drain current	$V_R = 600 \text{ V}$ $V_R = 600 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		30 2	μA mA
V_F	forward voltage drop	$I_F = 30 \text{ A}$ $I_F = 60 \text{ A}$ $I_F = 30 \text{ A}$ $I_F = 60 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.26 3.11 2.21 3.17	V V
I_{FAV}	average forward current	$T_C = 85^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ\text{C}$		30	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		1.17 31	V $\text{m}\Omega$
R_{thJC}	thermal resistance junction to case				0.7	K/W
R_{thCH}	thermal resistance case to heatsink			0.3		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		180	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 \text{ V}$	$T_{VJ} = 45^\circ\text{C}$		200	A
C_J	junction capacitance	$V_R = 400 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		16	pF
I_{RM}	max. reverse recovery current		$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		13 17	A A
t_{rr}	reverse recovery time	$I_F = 30 \text{ A}; V_R = 300 \text{ V}$ $-di_F/dt = 600 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		40 60	ns ns

Package TO-247

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_d	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

Product Marking

Part description

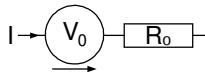
D = Diode
H = Sonic Fast Recovery Diode
G = extreme fast
60 = Current Rating [A]
C = Common Cathode
600 = Reverse Voltage [V]
HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG60C600HB	DHG60C600HB	Tube	30	503108

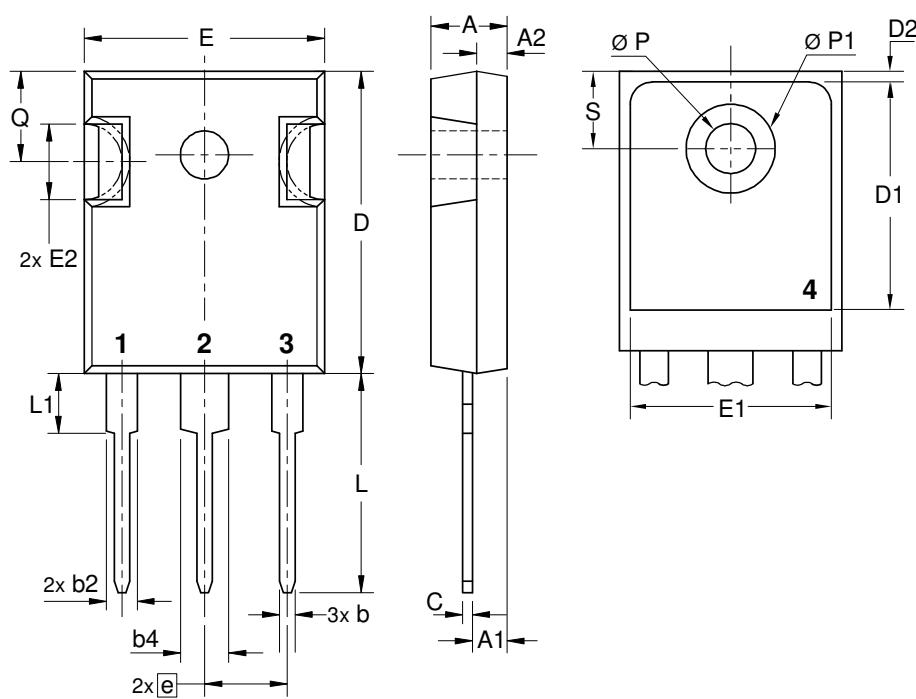
Similar Part	Package	Voltage class
DSEC60-06A	TO-247AD (3)	600
DSEC60-06B	TO-247AD (3)	600
DSEC59-06BC	ISOPLUS220AB (3)	600

Equivalent Circuits for Simulation
^{*}on die level

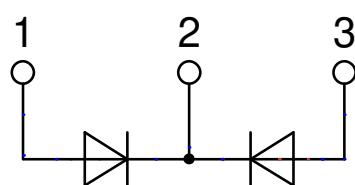
 $T_{VJ} = 150^\circ\text{C}$

	Fast Diode
$V_{0\max}$	threshold voltage
$R_{0\max}$	slope resistance *

1.17 V
28 mΩ

Outlines TO-247


Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



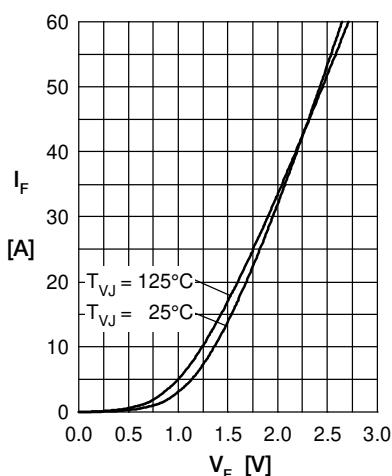
Fast Diode


Fig. 1 Typ. Forward current versus V_F

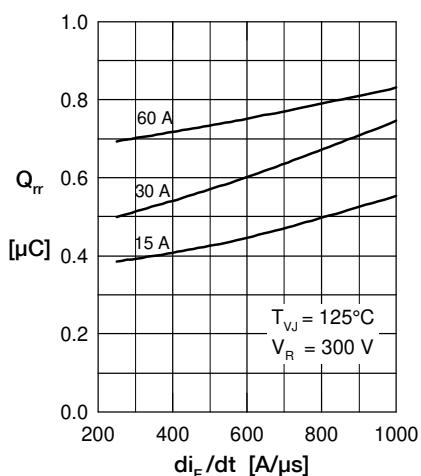


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

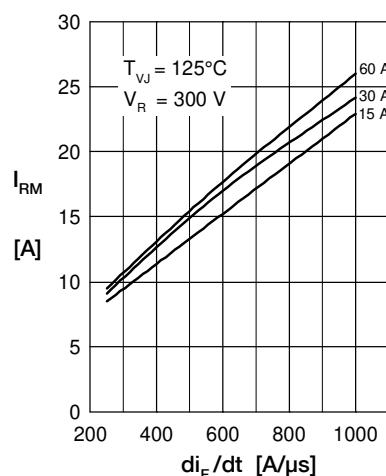


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

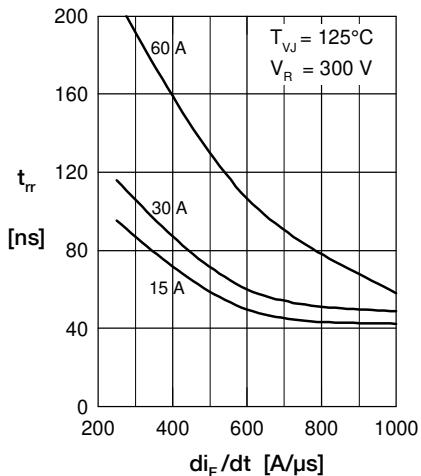


Fig. 4 Dynamic parameters Q_{rr}, I_{RM} versus T_{VJ}

Fig. 5 Typ. recovery time t_{rr} versus di/dt

Fig. 6 Typ. recovery energy E_{rec} versus di/dt

